Michael V Yakushev

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147 papers	1,101 citations	19 h-index	25 g-index
152 ext. papers	1,216 ext. citations	1.6 avg, IF	3.75 L-index

#	Paper	IF	Citations
147	Optical properties of high quality Cu2ZnSnSe4 thin films. *Applied Physics Letters*, **2011**, 99, 062104	3.4	77
146	Molecular-beam epitaxy of mercury-cadmium-telluride solid solutions on alternative substrates. *Semiconductors*, **2001**, 35, 1045-1053	0.7	47
145	Excited states of the free excitons in CuInSe2 single crystals. *Applied Physics Letters*, **2010**, 97, 152110	3.4	36
144	Energy of excitons in CuInS2 single crystals. *Applied Physics Letters*, **2006**, 88, 011922	3.4	33
143	Electronic and structural characterisation of Cu3BiS3 thin films for the absorber layer of sustainable photovoltaics. *Thin Solid Films*, **2014**, 562, 195-199	2.2	31
142	HgCdTe heterostructures on Si (310) substrates for midinfrared focal plane arrays. *Semiconductors*, **2011**, 45, 385-391	0.7	30
141	Influence of the copper content on the optical properties of CZTSe thin films. *Solar Energy Materials and Solar Cells*, **2017**, 168, 69-77	6.4	29
140	Excitation power and temperature dependence of excitons in CuInSe2. *Journal of Applied Physics*, **2012**, 111, 093507	2.5	29
139	Optical properties of high-quality CuInSe2 single crystals. *Applied Physics Letters*, **2000**, 77, 2542-2544	3.4	29
138	Structural and optical properties of thin films of Cu(In,Ga)Se2 semiconductor compounds. *Journal of Applied Spectroscopy*, **2010**, 77, 371-377	0.7	27
137	Excited states of the A free exciton in CuInS2. *Applied Physics Letters*, **2008**, 92, 111908	3.4	26
136	Changes in the opto-electronic properties of CuInSe2 following ion implantation. *Journal of Electronic Materials*, **1991**, 20, 659-663	1.9	25
135	Low energy ion beam etching of CuInSe2 surfaces. *Journal of Vacuum Science and Technology A: Vacuum, Surfaces and Films*, **1999**, 17, 19-25	2.9	24
134	First-principles study of deformation behavior and structural defects in CuInSe2 and Cu(In,Ga)Se2. *Physical Review B*, **2006**, 73,	3.3	22
133	Diamagnetic shift of the A free exciton in CuGaSe2 single crystals. *Applied Physics Letters*, **2010**, 97, 162104	3.4	20
132	Modeling hydrogen in CuInSe2 and CuInS2 solar cell materials using implanted muons. *Physical Review B*, **1999**, 59, 1912-1916	3.3	20
131	Influence of proton implantation on the properties of CuInSe2 single crystals (II). *Crystal Research and Technology*, **1994**, 29, 417-426	1.3	20

130	Photoluminescence of Hg1 □x Cd x Te based heterostructures grown by molecular-beam epitaxy. *Semiconductors*, **2011**, 45, 872-879	0.7	19
129	Optical properties and band gap energy of CuInSe2 thin films prepared by two-stage selenization process. *Journal of Physics and Chemistry of Solids*, **2003**, 64, 2005-2009	3.9	19
128	Photoacoustic spectroscopy use in the analysis of ion-implanted CuInSe2 single crystals. *Review of Scientific Instruments*, **1995**, 66, 4095-4101	1.7	17
127	Fabrication and characterisation of Cu(In,Ga)Se2 solar cells on polyimide. *Thin Solid Films*, **2011**, 519, 7264-7267	2.2	16
126	Influence of proton implantation on the properties of CuInSe2 single crystals (I). Ion channeling study of lattice damage. *Crystal Research and Technology*, **1994**, 29, 125-132	1.3	16
125	Effect of plasma hydrogenation on the defect properties of CuInSe2 single crystals. *Crystal Research and Technology*, **1994**, 29, 427-437	1.3	16
124	Spectroscopic and electrical signatures of acceptor states in solution processed Cu2ZnSn(S,Se)4 solar cells. *Journal of Materials Chemistry C*, **2017**, 5, 12720-12727	7.1	15
123	Radiative recombination in Cu2ZnSnSe4thin films with Cu deficiency and Zn excess. *Journal Physics D: Applied Physics*, **2015**, 48, 475109	3	14
122	A Rutherford backscattering-channelling and Raman study of CuInSe2 single crystal surfaces. *Journal of Materials Science: Materials in Electronics*, **1996**, 7, 155	2.1	14
121	Anisotropy of effective masses in CuInSe2. *Applied Physics Letters*, **2012**, 101, 262101	3.4	13
120	Optical spectroscopy studies of Cu2ZnSnSe4 thin films. *Thin Solid Films*, **2015**, 582, 154-157	2.2	12
119	Excitons in high-quality CuInS2 single crystals. *Thin Solid Films*, **2006**, 511-512, 130-134	2.2	12
118	XPS Analysis of Bridgman-grown CuInTe2 and of its Native Oxide. *Crystal Research and Technology*, **1996**, 31, 75-85	1.3	12
117	A photoelectron spectroscopy study of the electronic structure evolution in CuInSe2-related compounds at changing copper content. *Applied Physics Letters*, **2012**, 101, 111607	3.4	11
116	Magneto-photoluminescence study of radiative recombination in CuInSe2 single crystals. *Journal of Physics and Chemistry of Solids*, **2003**, 64, 2011-2016	3.9	10
115	Electrical Properties of CuInSe2 Single Crystals Implanted with Xenon. *Crystal Research and Technology*, **1993**, 28, 267-272	1.3	10
114	Defects in the crystal structure of Cd x Hg1 □x Te layers grown on the Si (310) substrates. *Semiconductors*, **2011**, 45, 926-934	0.7	9
113	Diamagnetic shifts of free excitons in CuInS2 in magnetic fields. *Applied Physics Letters*, **2009**, 94, 042109	3.4	9

112	Optical spectroscopy of excitonic states in CuInSe2. *Semiconductors*, **2000**, 34, 534-537	0.7	9
111	The effects of ion implantation on the microstructure of CuInSe2 single crystals. *Philosophical Magazine A: Physics of Condensed Matter, Structure, Defects and Mechanical Properties*, **1996**, 73, 1131-1145		9
110	Comparative optical absorption and photoreflectance study of n-type CuInSe2 single crystals. *Crystal Research and Technology*, **1994**, 29, 719-726	1.3	9
109	A photoluminescence study of CuInSe2single crystals ion implanted with 5 keV hydrogen. *Journal Physics D: Applied Physics*, **2016**, 49, 105108	3	8
108	A photoluminescence study of excitonic grade CuInSe2 single crystals irradiated with 6 MeV electrons. *Journal of Applied Physics*, **2015**, 118, 155703	2.5	8
107	Resonant photoemission spectroscopy of Cu(InGa)Se2 materials for solar cells. *Bulletin of the Russian Academy of Sciences: Physics*, **2013**, 77, 1123-1126	0.4	8
106	Temperature dependence of excitonic emission in CuInSe2. *Physica Status Solidi C: Current Topics in Solid State Physics*, **2009**, 6, 1082-1085		8
105	Dependence of the electrical parameters of MBE-grown Cd x Hg1 □x Te films on the level of doping with indium. *Semiconductors*, **2008**, 42, 648-650	0.7	8
104	Effects of D+ implantation of CIGS thin films through a CdS layer. *Thin Solid Films*, **2001**, 387, 201-204	2.2	8
103	On the redistribution of 10keV hydrogen in CuInSe2. *Radiation Effects and Defects in Solids*, **1998**, 145, 85-105	0.9	8
102	Defect levels and hyperfine constants of hydrogen in beryllium oxide from hybrid-functional calculations and muonium spectroscopy. *Philosophical Magazine*, **2017**, 97, 2108-2128	1.6	7
101	Investigation of the Structural, Optical and Electrical Properties of Cu3BiS3 Semiconducting Thin Films. *Energy Procedia*, **2014**, 60, 166-172	2.3	7
100	Energy of free excitons in CuInSe2 single crystals. *Applied Physics Letters*, **2003**, 82, 3233-3235	3.4	7
99	Studies of the Effects of Ion-Implantation and Electron Beam Irradiation on CuInSe2 Single Crystals. *Materials Research Society Symposia Proceedings*, **1992**, 262, 1097		7
98	Stimulated emission and lasing in Cu(In,Ga)Se2thin films. *Journal Physics D: Applied Physics*, **2016**, 49, 095106	3	6
97	Dislocations in CdTe heteroepitaxial structures on GaAs(301) and Si(301) substrates. *Optoelectronics, Instrumentation and Data Processing*, **2014**, 50, 234-240	0.6	6
96	Incorporation of hydrogen in CuInSe2: Improvements of the structure. *Journal of Vacuum Science and Technology A: Vacuum, Surfaces and Films*, **2011**, 29, 051201	2.9	6
95	Capacitive Properties of Metal□Insulator□Semiconductor Systems Based on an HgCdTe nBn Structure Grown by Molecular Beam Epitaxy. *Journal of Communications Technology and Electronics*, **2019**, 64, 289-293	0.5	5

94	CdHgTe heterostructures on large-area Si(310) substrates for infrared photodetector arrays of the short-wavelength spectral range. *Semiconductors*, **2014**, 48, 767-771	0.7	5
93	Effects of magnetic fields on free excitons in CuInSe2. *Physica Status Solidi C: Current Topics in Solid State Physics*, **2009**, 6, 1086-1088		5
92	Low-temperature photoluminescence in AgGaSe2 single crystals. *Technical Physics*, **2004**, 49, 335-337	0.5	5
91	Diffusion effects at the Au/p-CuInSe2 contact studied by XPS. *Crystal Research and Technology*, **2003**, 38, 676-683	1.3	5
90	Photosensitivity of photocells based on ZnO/CdS/Cu(In, Ga)Se2 heterostructures and exposed to γ-ray radiation. *Semiconductors*, **2005**, 39, 1406	0.7	5
89	A Photoluminescence Study of Hydrogen-Implanted Cu(InGa)Se2Thin Films. *Japanese Journal of Applied Physics*, **2000**, 39, 320	1.4	5
88	Photoacoustic Spectroscopy of Defect States in Etched and Air-annealed CuInSe2 Single Crystals. *Crystal Research and Technology*, **1995**, 30, 517-530	1.3	5
87	Diode n-p CuInSe2 Structures Fabricated by Oxygen Implantation. *Crystal Research and Technology*, **1990**, 25, 1299-1302	1.3	5
86	Strong interband Faraday rotation in 3D topological insulator Bi2Se3. *Scientific Reports*, **2016**, 6, 19087	4.9	5
85	Influence of the growth method on the photoluminescence spectra and electronic properties of CuInS2 single crystals. *Journal of Luminescence*, **2017**, 186, 123-126	3.8	4
84	The band structure of CuInTe2 studied by optical reflectivity. *Applied Physics Letters*, **2019**, 114, 062103	3.4	4
83	Methodological and instrumental problems in high-precision in situ ellipsometry diagnostics of the mercury cadmium telluride layer composition in molecular beam epitaxy. *Instruments and Experimental Techniques*, **2016**, 59, 857-864	0.5	4
82	Photoluminescence of CdHgTe solid solutions subjected to low-energy ion treatment. *Semiconductors*, **2014**, 48, 195-198	0.7	4
81	High-temperature photoluminescence of CdHgTe solid solutions grown by molecular-beam epitaxy. *Technical Physics*, **2013**, 58, 1536-1539	0.5	4
80	Electrical and optical properties of CdHgTe films grown by molecular-beam epitaxy on silicon substrates. *Semiconductors*, **2012**, 46, 1341-1345	0.7	4
79	Surface micromorphology of CdTe(310) layers grown by molecular beam epitaxy. *Journal of Surface Investigation*, **2010**, 4, 64-70	0.5	4
78	XPS and XPD investigation of (112) CuInSe2 and Cu(InGa)Se2 surfaces. *Thin Solid Films*, **2004**, 451-452, 137-140	2.2	4
77	Effects of deviation from stoichiometry on excitons in CuInSe2 single crystals. *Thin Solid Films*, **2003**, 431-432, 190-192	2.2	4

76	Spontaneous formation of the periodic composition-modulated nanostructure in CdxHg1 Te films. *Semiconductors*, **2003**, 37, 1331-1335	0.7	4
75	In situ XPS investigations of ion beam hydrogenation of CuInSe2. *Thin Solid Films*, **2001**, 387, 185-188	2.2	4
74	Photoluminescence spectra of the AgGaTe2 single crystals doped with hydrogen. *Optics and Spectroscopy (English Translation of Optika I Spektroskopiya)*, **2000**, 88, 377-379	0.7	4
73	Hydrogen Diffusion in Chalcopyrite Solar Cell Materials. *Materials Research Society Symposia Proceedings*, **1998**, 513, 177		4
72	CdHgTe heterostructures for new-generation IR photodetectors operating at elevated temperatures. *Semiconductors*, **2016**, 50, 1626-1629	0.7	4
71	Characterization of vacancy defects in Cu(In,Ga)Se2 by positron annihilation spectroscopy. *AIP Advances*, **2016**, 6, 125031	1.5	4
70	Effects of Ar+ etching of Cu2ZnSnSe4 thin films: An x-ray photoelectron spectroscopy and photoluminescence study. *Journal of Vacuum Science and Technology B:Nanotechnology and Microelectronics*, **2018**, 36, 061208	1.3	4
69	Ellipsometric Method for Measuring the CdTe Buffer-Layer Temperature in the Molecular-Beam Epitaxy of CdHgTe. *Semiconductors*, **2019**, 53, 132-137	0.7	3
68	Possibilities of Characterizing the Crystal Parameters of CdxHg1 xTe Structures on GaAs Substrates by the Method of Generation of the Probe-Radiation Second Harmonic in Reflection Geometry. *Physics of the Solid State*, **2020**, 62, 252-259	0.8	3
67	Photodetectors with 384 288 Matrix Elements for the Infrared Range of 8 10 Microns. *Journal of Communications Technology and Electronics*, **2019**, 64, 1024-1029	0.5	3
66	Landau levels of the C-exciton in CuInSe2 studied by magneto-transmission. *Applied Physics Letters*, **2014**, 105, 142103	3.4	3
65	Effect of orientation of the substrate on the conditions of growth of HgTe films by molecular beam epitaxy. *Inorganic Materials*, **2009**, 45, 13-18	0.9	3
64	Structural and optical properties of CdS/Cu(In,Ga)Se2 heterostructures irradiated by high-energy electrons*. *Journal of Applied Spectroscopy*, **2010**, 77, 668-674	0.7	3
63	Effect of ray radiation on photosensitivity of ZnO/CuIn3Se5 heterojunctions. *Semiconductors*, **2006**, 40, 64-66	0.7	3
62	Defect formation in thin films of the semiconductor compound Cu(In,Ga)Se2 when bombarded by protons. *Journal of Applied Spectroscopy*, **2006**, 73, 928-931	0.7	3
61	Photosensitivity of structures based on I-IIIn-VIm ternary compounds containing ordered vacancies. *Semiconductors*, **2002**, 36, 1132-1135	0.7	3
60	Comparative study of Er-implanted Si, ZnAs2 and CuInSe2. *Materials Science and Engineering B: Solid-State Materials for Advanced Technology*, **2003**, 105, 175-178	3.1	3
59	Radiation-induced defects in thin Cu(In,Ga)Se2 films on exposure to high-energy electron irradiation. *Journal of Applied Spectroscopy*, **2005**, 72, 883-886	0.7	3

58	Optical Properties of Excitonic-Grade CuInSe2Single Crystals. *Japanese Journal of Applied Physics*, **2000**, 39, 92	1.4	3
57	A rutherford backscattering spectrometry study of Zn implanted BeO single crystals. *Radiation Effects and Defects in Solids*, **1999**, 150, 157-160	0.9	3
56	Optical Investigation of Defects in p-type CuInSe2 Single Crystals. *Crystal Research and Technology*, **1996**, 31, 63-74	1.3	3
55	A luminescence study of Cu2ZnSnSe4/Mo/glass films and solar cells with near stoichiometric copper content. *Journal Physics D: Applied Physics*, **2019**, 52, 055502	3	3
54	A Megapixel Matrix Photodetector of the Middle Infrared Range. *Journal of Communications Technology and Electronics*, **2019**, 64, 1011-1015	0.5	2
53	Defects in mercury-cadmium telluride heteroepitaxial structures grown by molecular-beam epitaxy on silicon substrates. *Semiconductors*, **2016**, 50, 208-211	0.7	2
52	Effect of mechanical compression on Cu(In,Ga)Se2 films: micro-structural and photoluminescence analysis. *RSC Advances*, **2014**, 4, 5141	3.7	2
51	Photoelectric characteristics of diodes in prototype photosensitive pixels for a monolithic array infrared photodetector. *Semiconductors*, **2012**, 46, 535-540	0.7	2
50	Magnetic field effect on free and bound excitons in chalcopyrite CuInS2. *Journal of Applied Spectroscopy*, **2007**, 74, 415-420	0.7	2
49	Optical spectroscopy of free excitons in a CuInS2 chalcopyrite semiconductor compound. *Semiconductors*, **2008**, 42, 29-33	0.7	2
48	Fabrication and photosensitivity of heterojunctions based on CuIn3Se5 crystals. *Semiconductors*, **2004**, 38, 1192-1197	0.7	2
47	Ion channeling study of defects in CuInTe2 single crystals. *Crystal Research and Technology*, **1995**, 30, 121-128	1.3	2
46	Parametric Model of the Optical Constant Spectra of Hg1 xCdxTe and Determination of the Compound Composition. *Optics and Spectroscopy (English Translation of Optika I Spektroskopiya)*, **2020**, 128, 1948-1953	0.7	2
45	The Effect of the Growth Temperature on the Passivating Properties of the Al2O3 Films Formed by Atomic Layer Deposition on the CdHgTe Surface. *Technical Physics Letters*, **2020**, 46, 741-744	0.7	2
44	Molecular Beam Epitaxy of CdHgTe: Current State and Horizons. *Optoelectronics, Instrumentation and Data Processing*, **2020**, 56, 456-469	0.6	2
43	Express Characterization of Crystalline Perfection of CdxHg1 Te Structures by Reflection Second Harmonic Generation of Probing Radiation. *Optoelectronics, Instrumentation and Data Processing*, **2019**, 55, 447-454	0.6	2
42	A Magneto-Reflectivity Study of CuGaSe2 Single Crystals. *Physica Status Solidi - Rapid Research Letters*, **2019**, 13, 1800374	2.5	2
41	A PL and PLE Study of High Cu Content Cu2ZnSnSe4 Films on Mo/Glass and Solar Cells. *Physics of the Solid State*, **2019**, 61, 908-917	0.8	1

40	Excitons in PL Spectra of Cu(In,Ga)Se2 Single Crystals. *Physics of the Solid State*, **2019**, 61, 918-924	0.8	1
39	HgCdTe-Based 640 □512 Matrix Midwave Infrared Photodetector. *Journal of Communications Technology and Electronics*, **2020**, 65, 316-320	0.5	1
38	Investigation of the Strongly Correlated Two-Hole State of Copper in Resonant Photoemission States of Chalcogenide Materials for Photovoltaics. *Physics of Metals and Metallography*, **2018**, 119, 520-522	1.2	1
37	Influence of Chemical Composition Heterogeneity on the Spectral Position of the Fundamental Absorption Edge of Cu(In, Ga)Se2 Solid Solutions. *Journal of Applied Spectroscopy*, **2014**, 81, 404-410	0.7	1
36	Dual-wavelength stimulated emission from a double-layer Cd x Hg1 □x Te structure at wavelengths of 2 and 3 □m. *JETP Letters*, **2013**, 97, 358-361	1.2	1
35	Ion channeling in CuInSe2 single crystals. *Nuclear Instruments & Methods in Physics Research B*, **2013**, 299, 24-28	1.2	1
34	Excited States of the A and B Free Excitons in CuInSe2. *Japanese Journal of Applied Physics*, **2011**, 50, 05FC03	1.4	1
33	Infrared focal plane assemblies based on HgCdTe/Si(310) heterostructure. *Technical Physics Letters*, **2011**, 37, 148-150	0.7	1
32	Photoluminescence of CuInS2 single crystals grown by traveling heater and chemical vapor transport methods. *Journal of Applied Spectroscopy*, **2009**, 76, 215-219	0.7	1
31	Interaction of cadmium vapor with the surface of Cd x Hg1□ Te layers during molecular beam epitaxial growth on GaAs substrates. *Inorganic Materials*, **2008**, 44, 366-370	0.9	1
30	Observation of antiphase domains in CdxHg1□ Te films on silicon by the phase contrast method in atomic force microscopy. *JETP Letters*, **2005**, 82, 292-296	1.2	1
29	Optical and Structural Properties of HgCdTe Solid Solutions with a High CdTe Content. *Semiconductors*, **2020**, 54, 1561-1566	0.7	1
28	Excited States of the A and B Free Excitons in CuInSe2. *Japanese Journal of Applied Physics*, **2011**, 50, 05FC03	1.4	1
27	RBS-channeling study of radiation damage in Ar+ implanted CuInSe2 crystals. *Journal of Vacuum Science and Technology A: Vacuum, Surfaces and Films*, **2016**, 34, 051203	2.9	1
26	Effects of selenisation temperature on photoluminescence and photoluminescence excitation spectra of ZnO/CdS/Cu2ZnSnSe4/Mo/glass. *Thin Solid Films*, **2019**, 672, 146-151	2.2	1
25	Radiative Recombination at Ion-Induced Defects in Cu(In,Ga)Se2 Alloy Thin Films. *Semiconductors*, **2021**, 55, 168-174	0.7	1
24	Structural Characteristics and Photoluminescence of Thin Films of Cu(In1□gax)(Syse1□)2 Solid Solutions. *Journal of Applied Spectroscopy*, **2021**, 88, 27-32	0.7	1
23	An Optical Study of Disordering in Cadmium Mercury Telluride Solid Solutions. *Technical Physics Letters*, **2019**, 45, 553-556	0.7	0

22	Photoluminescence, stimulated and laser emission in CuInSe2 crystals. *Applied Physics Letters*, **2021**, 119, 212103	3.4	0
21	Advanced Design of Scanning Infrared Focal Plane Arrays. *Optoelectronics, Instrumentation and Data Processing*, **2018**, 54, 569-575	0.6	0
20	Diffusion Limitation of Dark Current in the nBn Structures Based on the MBE HgCdTe. *Journal of Communications Technology and Electronics*, **2022**, 67, 308-312	0.5	0
19	Mapping the Energetics of Defect States in CuZnSnS films and the Impact of Sb Doping.. *ACS Applied Energy Materials*, **2022**, 5, 3933-3940	6.1	0
18	The g-factor of CuGaSe2 studied by circularly polarised magneto-reflectance. *Journal Physics D: Applied Physics*, **2020**, 53, 17LT02	3	
17	Stimulated Emission and Optical Properties of Solid Solutions of Cu(In,Ga)Se2 Direct Band Gap Semiconductors. *Journal of Applied Spectroscopy*, **2018**, 85, 267-273	0.7	
16	The Effect of Copper on the Electronic Structure and Effective Masses of CuIn5Se8 Single Crystals Revealed by Angle-Resolved Photoemission Spectroscopy. *Physics of Metals and Metallography*, **2018**, 119, 430-435	1.2	
15	Impact of the Graded-Gap Layer on the Admittance of MIS Structures Based on MBE-Grown n-Hg1 □ xCd x Te (x = 0.220.23) with the Al2O3 Insulator. *Journal of Communications Technology and Electronics*, **2018**, 63, 281-284	0.5	
14	HgCdTe heterostructures on Si(310) substrates for infrared photodetectors. *Optoelectronics, Instrumentation and Data Processing*, **2009**, 45, 301-307	0.6	
13	Monitoring the composition of the Cd1 □z Zn z Te heteroepitaxial layers by spectroscopic ellipsometry. *Semiconductors*, **2010**, 44, 59-65	0.7	
12	Modification of the CuInSe2 Crystal Surface during Polishing and Annealing. *Crystal Research and Technology*, **1997**, 32, 155-161	1.3	
11	Surface morphology of a Si(310) substrate used for molecular beam epitaxy of CdHgTe: II. Si(310) surface annealed in As4 vapors. *Journal of Surface Investigation*, **2008**, 2, 433-439	0.5	
10	The effect of a surface layer on determination of the dielectric functions of ZnTe films by the ellipsometric technique. *Optics and Spectroscopy (English Translation of Optika I Spektroskopiya)*, **2002**, 92, 780-783	0.7	
9	Photoelectric Properties of the In/CuIn3Se5 and In/CuGa3Se5 Structures. *Journal of Applied Spectroscopy*, **2002**, 69, 602-605	0.7	
8	Molecular static model of CuInSe2 crystal: Energy properties of some structural defects. *Physics of the Solid State*, **2000**, 42, 1643-1647	0.8	
7	Photoluminescence Studies of Low Energy Hydrogen-Implanted AgGaTe2Single Crystals. *Japanese Journal of Applied Physics*, **2000**, 39, 114	1.4	
6	A Raman Scattering, Ion Channelling and Photoluminescence Study of Argon Ion Radiation Damage in Cu(Ga,In)Se2 - Dose Dependence and Dose Rate Effects. *Materials Research Society Symposia Proceedings*, **1998**, 540, 85		
5	A Magneto-Reflectivity Study of CuInTe2 Single Crystals. *Physica Status Solidi (B): Basic Research*, **2020**, 257, 1900464	1.3	

4	Spontaneous and Stimulated Emission in Thin Films of Cu(In1 xGax)(SySe1 y)2 Solid Solutions in the omposition of Solar Cells. *Semiconductors*, **2020**, 54, 1247-1253	0.7
3	Luminescence and Stimulated Emission of Polycrystalline Cu(In,Ga)Se2 Films Deposited by Magnetron-Assisted Sputtering. *Semiconductors*, **2018**, 52, 1238-1243	0.7
2	Ellipsometric In Situ Methods of Temperature Control in the Technology of Growing MBE MCT Layers. *Optoelectronics, Instrumentation and Data Processing*, **2021**, 57, 476-484	0.6
1	Admittance of MIS Structures Based on nBn Systems of Epitaxial HgCdTe for Detection in the 3 5 n Spectral Range. *Technical Physics Letters*, **2021**, 47, 629-632	0.7